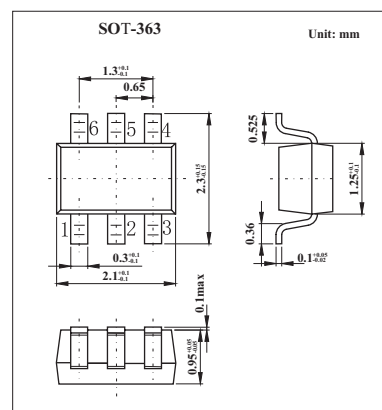


Dual Schottky Barrier Diodes

MBD110DWT1
MBD330DWT1;MBD770DWT1

■ Features

- Extremely Low Minority Carrier Lifetime
- Very Low Capacitance
- Low Reverse Leakage

■ Absolute Maximum Ratings $T_A = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	7	Vdc
		30	
		70	
Forward Power Dissipation $T_A = 25^\circ\text{C}$	P_F	120	mA
Junction Temperature	T_J	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

MBD110DWT1 MBD330DWT1;MBD770DWT1

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	MBD110DWT1 MBD330DWT1 MBD770DWT1	V _{BR(R)}	I _R = 10 μA	7.0	10	Volts
				30		
				70		
Diode Capacitance	MBD110DWT1	C _T	V _R = 0, f = 1.0 MHz	0.88	1.0	pF
Total Capacitance	MBD330DWT1	C _T	V _R = 15 Volts, f = 1.0 MHz	0.9	1.5	pF
	MBD770DWT1		V _R = 20 Volts, f = 1.0 MHz	0.5	1.0	
Reverse Leakage	MBD110DWT1	I _R	V _R = 3.0 V	0.02	0.25	μA
	MBD330DWT1		V _R = 25 V	13	200	nA _{dc}
	MBD770DWT1		V _R = 35 V	9	200	nA _{dc}
Noise Figure	MBD110DWT1	NF	f = 1.0 GHz	6		dB
Forward Voltage	MBD110DWT1	V _F	I _F = 10 mA	0.5	0.6	V _{dc}
	MBD330DWT1		I _F = 1.0 mA _{dc}	0.38	0.45	
			I _F = 10 mA	0.52	0.6	
			I _F = 1.0 mA _{dc}	0.47	0.5	
	MBD770DWT1		I _F = 10 mA	0.7	1.0	

■ Marking

Type	MBD110DWT1	MMBD330DWT1	MBD770DWT1
Marking	M4	T4	H5